NEC

NPN SILICON TRANSISTOR 2SC3622

DESCRIPTION

The 2SC3622 is designed for general-purpose applications requiring

High DC Current Gain.

This is suitable for all kind of driving, instead of Darlington

Transistor, or muting.

FEATURES

• High DC Current Gain.

 $h_{FE} = 1000 \text{ to } 3200 \text{ (@ } V_{CE} = 5.0 \text{ V, } I_{C} = 1.0 \text{ mA)}$

• Low Collector Saturation Voltage.

 $V_{CE(sat)} = 0.07 \text{ V TYP.}$ (@ $I_{C} = 50 \text{ mA}$, $I_{B} = 5.0 \text{ mA}$)

High V_{EBO} : V_{EBO} > 12 V

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Storage	e Temperature	to +1	50 °C
Junctio	on Temperature 150 °C	: Maxi	mum
Maximum	Power Dissipation (T _a = 25 °C)		
Total F	Power Dissipation	250	mW
Maximum	Voltages and Currents (T _a = 25 °C)		
V _{CBO}	Collector to Base Voltage	60	V
V_{CEO}	Collector to Emitter Voltage	50	٧
V_{EBO}	Emitter to Base Voltage	12	٧
lc	Collector Current	150	mΑ
l _B	Base Current	10	mΑ

PACKAGE DIMENSIONS in millimeters (inches) 5.2 MAX. (0.204 MAX.) (0.204 MAX.) (0.005) 1. EMITTER EIAJ : SC-43B 2. COLLECTOR JEDEC : TO-92 3. BASE IEC : PA33

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1*	DC Current Gain	1000	1800	3200	_	V _{CE} = 5.0 V, I _C = 1.0 mA
hFE2*	DC Current Gain	200	350			$V_{CE} = 5.0 \text{ V, I}_{C} = 100 \text{ mA}$
fT	Gain Bandwidth Product		250		MHz	$V_{CE} = 5.0 \text{ V, } I_{E} = -10 \text{ mA}$
Cob	Output Capacitance		3.0		рF	$V_{CB} = 5.0 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$
ton	Turn-on Time		0.13		μs	$/V_{CC} = 10 \text{ V}, V_{BE(off)} = -2.7 \text{ V}$
tf	Storage Time		0.72		μs	I _C = 50 mA
^t off	Turn-off Time		1.22		μs	$l_{B1} = -l_{B2} = 1.0 \text{ mA}$
¹ CBO	Collector Cutoff Current			100	nΑ	$V_{CB} = 50 \text{ V, } I_{E} = 0$
¹ EBO	Emitter Cutoff Current			100	nА	$V_{EB} = 10 V, I_{C} = 0$
VBE*	Base to Emitter Voltage		560		mV	$V_{CE} = 5.0 \text{ V, } I_{C} = 1.0 \text{ mA}$
VCE(sat)*	Collector Saturation Voltage		0.07	0.30	٧	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$
VBE(sat)*	Base Saturation Voltage		0.8	1.2	V	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$

^{*}Marked items are Pulse Test : PW 350 µs, Duty Cycle ≤ 2 %

Classification of hFE1

Rank	L	κ
Range	1000 to 2000	1600 to 3200

Test Conditions: $V_{CE} = 5.0 \text{ V}$, $I_{C} = 1.0 \text{ mA}$

TYPICAL CHARACTERISTICS (T_a = 25 °C)

